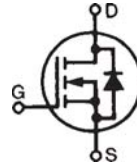


## HiPerFET™ Power MOSFET Q2-Class

### IXFL38N100Q2

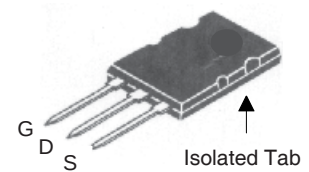
N-Channel Enhancement Mode  
Avalanche Rated, Low  $Q_g$ , Low Intrinsic  $R_G$   
High  $dV/dt$ , Low  $t_{rr}$



$$\begin{aligned} V_{DSS} &= 1000V \\ I_{D25} &= 29A \\ R_{DS(on)} &\leq 280m\Omega \\ t_{rr} &\leq 300ns \end{aligned}$$

| Symbol     | Test Conditions                                                          | Maximum Ratings |                  |
|------------|--------------------------------------------------------------------------|-----------------|------------------|
| $V_{DSS}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                          | 1000            | V                |
| $V_{DGR}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$    | 1000            | V                |
| $V_{GSS}$  | Continuous                                                               | $\pm 30$        | V                |
| $V_{GSM}$  | Transient                                                                | $\pm 40$        | V                |
| $I_{D25}$  | $T_C = 25^\circ\text{C}$                                                 | 29              | A                |
| $I_{DM}$   | $T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$               | 152             | A                |
| $I_A$      | $T_C = 25^\circ\text{C}$                                                 | 38              | A                |
| $E_{AS}$   | $T_C = 25^\circ\text{C}$                                                 | 5               | J                |
| $dV/dt$    | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ | 20              | V/ns             |
| $P_D$      | $T_C = 25^\circ\text{C}$                                                 | 380             | W                |
| $T_J$      |                                                                          | -55 ... +150    | $^\circ\text{C}$ |
| $T_{JM}$   |                                                                          | 150             | $^\circ\text{C}$ |
| $T_{stg}$  |                                                                          | -55 ... +150    | $^\circ\text{C}$ |
| $T_L$      | 1.6 mm (0.063 in.) from case for 10s                                     | 300             | $^\circ\text{C}$ |
| $T_{SOLD}$ | Plastic body for 10s                                                     | 260             | $^\circ\text{C}$ |
| $F_C$      | Mounting force                                                           | 30..120/6.7..27 | N/lbs            |
| $V_{ISOL}$ | 50/60 Hz, RMS $t = 1$ min<br>$I_{ISOL} \leq 1$ mA $t = 1$ s              | 2500<br>3000    | V~<br>V~         |
| Weight     |                                                                          | 10              | g                |

ISOPLUS264™ (IXFL)



G = Gate      D = Drain  
S = Source

### Features

- Electrically isolated mounting tab
- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance  
- easy to drive and to protect
- Fast intrinsic diode

### Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies
- DC choppers
- Pulse generation
- Laser drivers

### Advantages

- 2500 V~ Electrical isolation
- ISOPLUS 264™ package for clip or spring mounting
- Space savings
- High power density

| Symbol       | Test Conditions                                                | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |                     |
|--------------|----------------------------------------------------------------|-----------------------------------------------------------------------------------|------|---------------------|
|              |                                                                | Min.                                                                              | Typ. | Max.                |
| $BV_{DSS}$   | $V_{GS} = 0$ V, $I_D = 1$ mA                                   | 1000                                                                              |      | V                   |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 8$ mA                               | 3.0                                                                               |      | 5.5 V               |
| $I_{GSS}$    | $V_{GS} = \pm 30$ V, $V_{DS} = 0$ V                            |                                                                                   |      | $\pm 200$ nA        |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$<br>$V_{GS} = 0$ V $T_J = 125^\circ\text{C}$ |                                                                                   |      | 100 $\mu$ A<br>5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10$ V, $I_D = 19$ A, Note 1                          |                                                                                   |      | 280 m $\Omega$      |

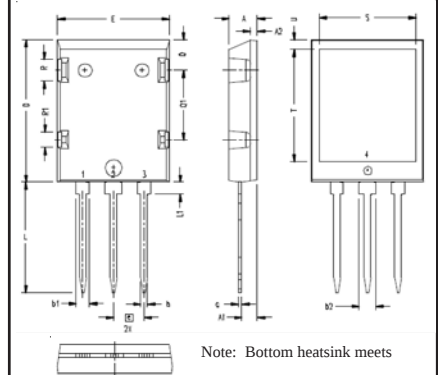
| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified)                                                                 | Characteristic Values |      |                        |
|--------------|---------------------------------------------------------------------------------------------------------------------------------------------|-----------------------|------|------------------------|
|              |                                                                                                                                             | Min.                  | Typ. | Max.                   |
| $g_{fs}$     | $V_{DS} = 20\text{V}$ , $I_D = 19\text{A}$ , Note 1                                                                                         | 24                    | 40   | S                      |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$                                                                            |                       | 13.5 | nF                     |
| $C_{oss}$    |                                                                                                                                             |                       | 1035 | pF                     |
| $C_{rss}$    |                                                                                                                                             |                       | 180  | pF                     |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 19\text{A}$<br>$R_G = 1\Omega$ (External) |                       | 25   | ns                     |
| $t_r$        |                                                                                                                                             |                       | 28   | ns                     |
| $t_{d(off)}$ |                                                                                                                                             |                       | 57   | ns                     |
| $t_f$        |                                                                                                                                             |                       | 15   | ns                     |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 19\text{A}$                                                                   |                       | 250  | nC                     |
| $Q_{gs}$     |                                                                                                                                             |                       | 60   | nC                     |
| $Q_{gd}$     |                                                                                                                                             |                       | 105  | nC                     |
| $R_{thJC}$   |                                                                                                                                             | 0.13                  |      | $0.33^\circ\text{C/W}$ |
| $R_{thCS}$   |                                                                                                                                             |                       |      | $^\circ\text{C/W}$     |

## Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified)                              | Characteristic Values |      |                   |
|----------|----------------------------------------------------------------------------------------------------------|-----------------------|------|-------------------|
|          |                                                                                                          | Min.                  | Typ. | Max.              |
| $I_S$    | $V_{GS} = 0\text{V}$                                                                                     |                       |      | 38 A              |
| $I_{SM}$ | Repetitive, pulse width limited by $T_{JM}$                                                              |                       |      | 152 A             |
| $V_{SD}$ | $I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1                                                              |                       |      | 1.5 V             |
| $t_{rr}$ | $I_F = 25\text{A}$ , $V_{GS} = 0\text{V}$<br>$-di/dt = 100\text{ A}/\mu\text{s}$<br>$V_R = 100\text{ V}$ |                       |      | 300 ns            |
| $Q_{RM}$ |                                                                                                          |                       |      | 1.4 $\mu\text{C}$ |
| $I_{RM}$ |                                                                                                          |                       |      | 9.0 A             |

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

## ISOPLUS264™ (IXFL) Outline



| SYM | INCHES   |       | MILLIMETERS |       |
|-----|----------|-------|-------------|-------|
|     | MIN      | MAX   | MIN         | MAX   |
| A   | .190     | .205  | 4.83        | 5.21  |
| A1  | .102     | .118  | 2.59        | 3.00  |
| A2  | .046     | .055  | 1.17        | 1.40  |
| b   | .045     | .055  | 1.14        | 1.40  |
| b1  | .087     | .102  | 2.21        | 2.59  |
| b2  | .111     | .126  | 2.82        | 3.20  |
| c   | .020     | .029  | 0.51        | 0.74  |
| D   | 1.020    | 1.040 | 25.91       | 26.42 |
| E   | .770     | .789  | 19.56       | 20.09 |
| e   | .215 BSC |       | 5.46 BSC    |       |
| L   | .780     | .820  | 19.81       | 20.83 |
| L1  | .080     | .102  | 2.03        | 2.59  |
| Q   | .210     | .235  | 5.33        | 5.97  |
| Q1  | .490     | .513  | 12.45       | 13.03 |
| R   | .150     | .180  | 3.81        | 4.57  |
| R1  | .100     | .130  | 2.54        | 3.30  |
| S   | .668     | .690  | 16.97       | 17.53 |
| T   | .801     | .821  | 20.34       | 20.85 |
| U   | .065     | .080  | 1.65        | 2.03  |

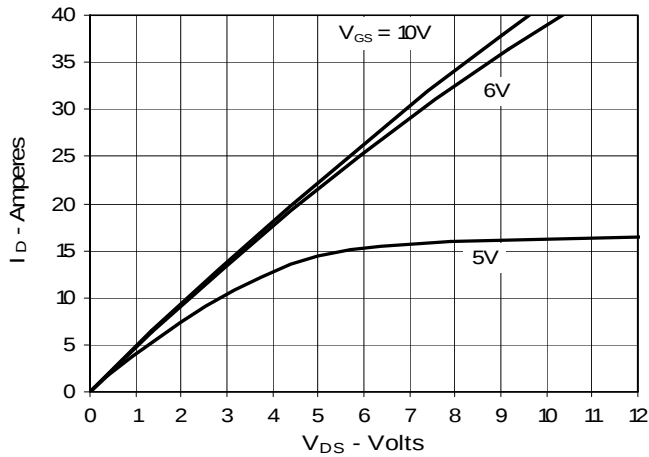
Ref: IXYS CO 0128

IXYS reserves the right to change limits, test conditions, and dimensions.

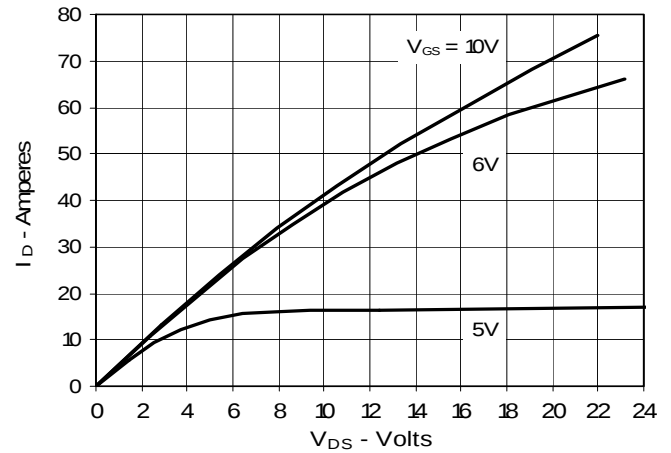
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

|           |           |           |           |              |              |              |              |              |             |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338B2 |
| 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |             |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |             |

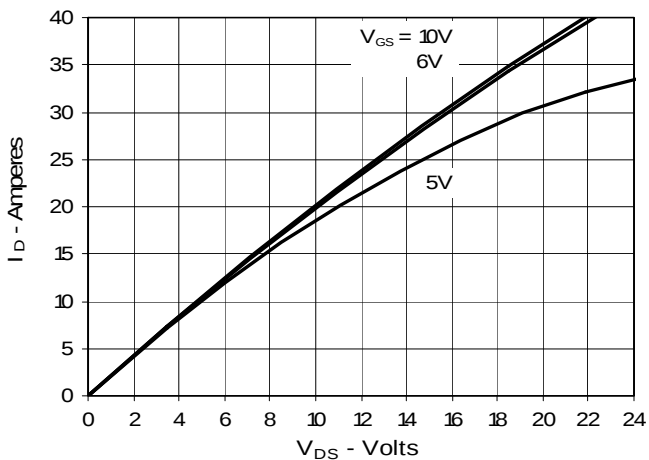
**Fig. 1. Output Characteristics**  
@ 25°C



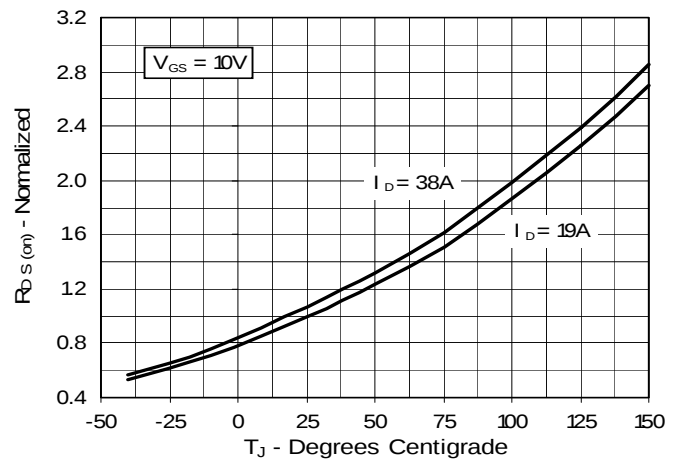
**Fig. 2. Extended Output Characteristics**  
@ 25°C



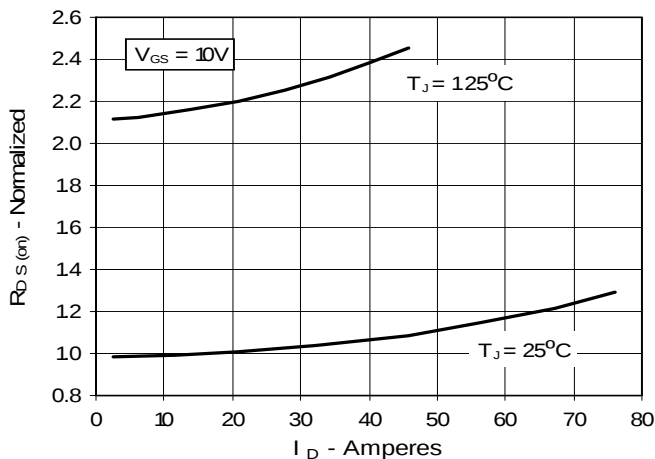
**Fig. 3. Output Characteristics**  
@ 125°C



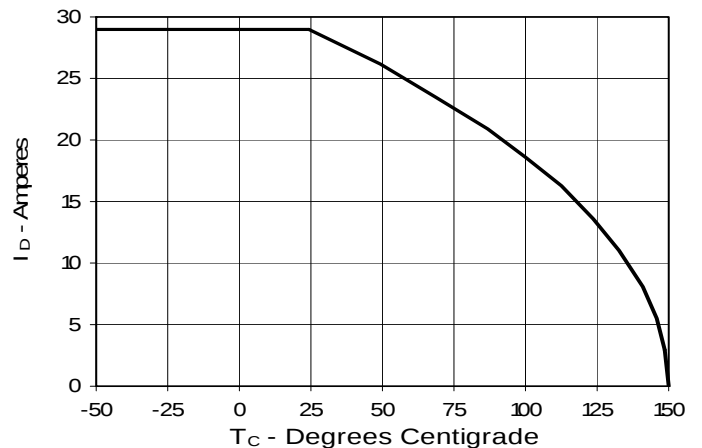
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 19A$**   
Value vs. Junction Temperature



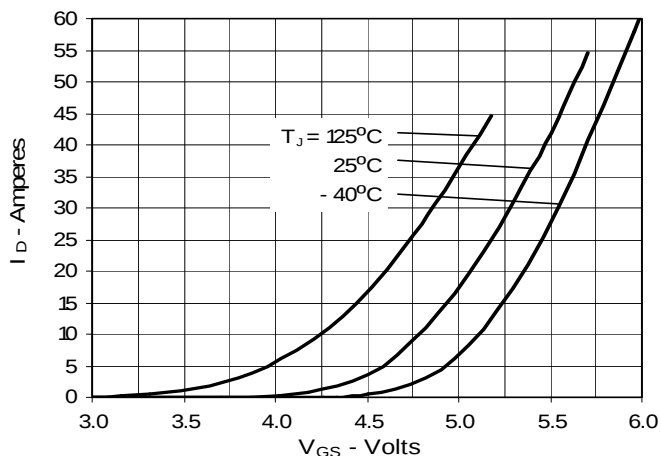
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 19A$**   
Value vs. Drain Current



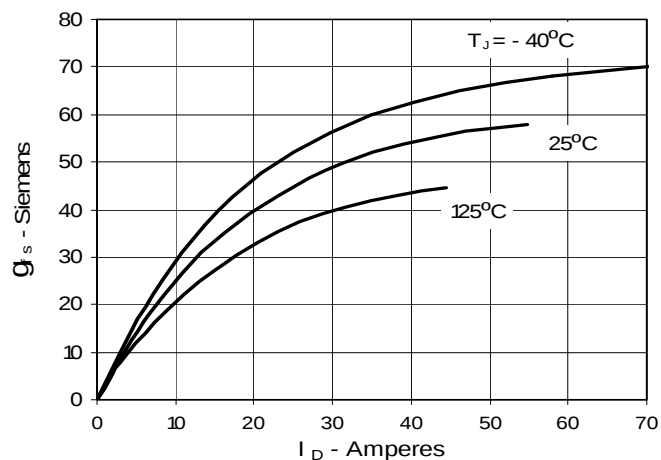
**Fig. 6. Drain Current vs. Case Temperature**



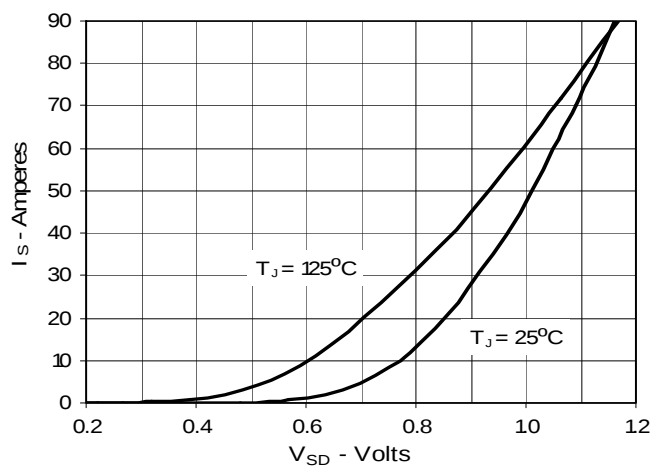
**Fig. 7. Input Admittance**



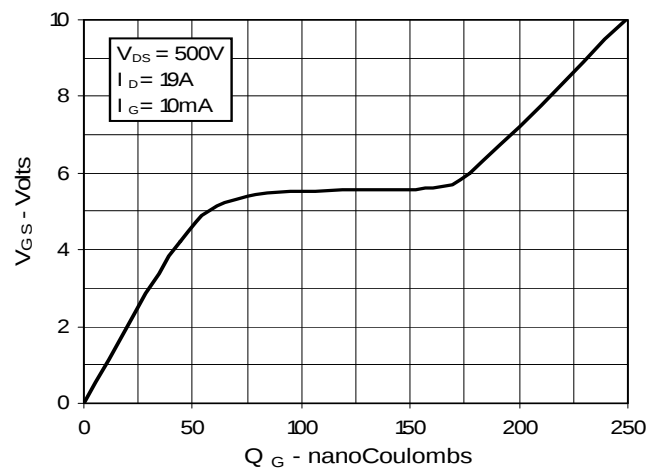
**Fig. 8. Transconductance**



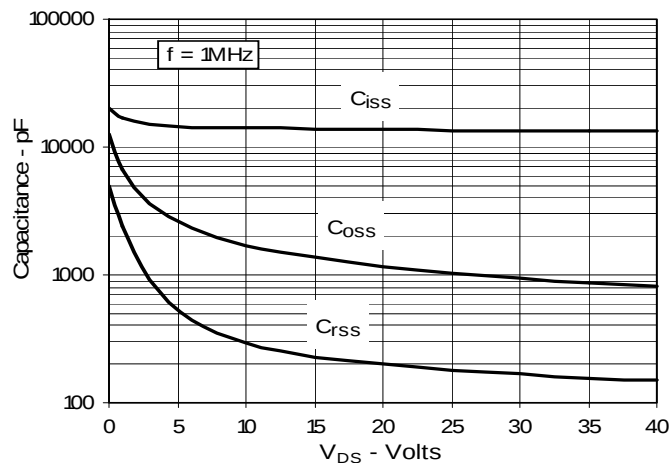
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**

